

N-channel 30 V, 10 mΩ logic level MOSFET in LFPAK33

19 September 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	54	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	55	W
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	8.1	10	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	5.5	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G-UF4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering inf	formation					
Type number	Package					
	Name	Description	Version			
BUK9M10-30E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M10-30E	91030E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; $T_j \le 175 \text{ °C}$	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	55	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	54	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	38	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	216	А

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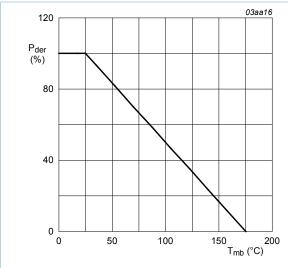
2/13

BUK9M10-30E

N-channel 30 V, 10 m Ω logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
l _S	source current	T _{mb} = 25 °C		-	45	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	216	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 54 \text{ A}; \ V_{sup} \leq 30 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} &= 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 4 \end{split}$	[3][4]	-	28.3	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

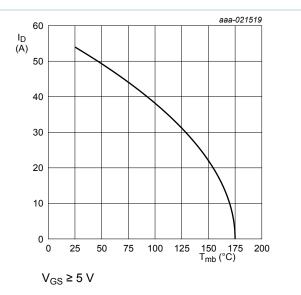
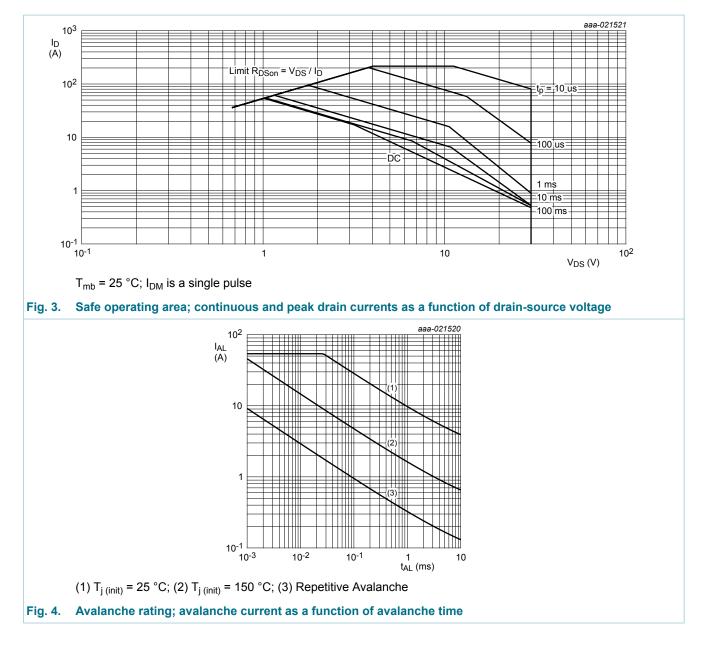


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 54A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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9. Thermal characteristics

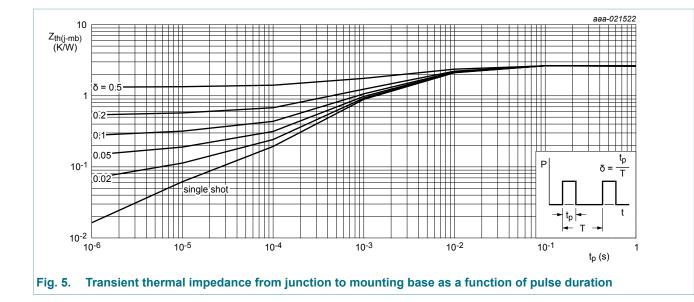
Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	2.46	2.75	K/W

BUK9M10-30E

4/13

BUK9M10-30E

N-channel 30 V, 10 m Ω logic level MOSFET in LFPAK33



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics	1	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.45	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	8.1	10	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	6.4	7.8	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 12	-	-	18.7	mΩ
Dynamic cl	naracteristics		1	1	-	
Q _{G(tot)}	total gate charge	I_D = 15 A; V_{DS} = 24 V; V_{GS} = 5 V;	-	12.2	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	2.6	-	nC

Product data sheet

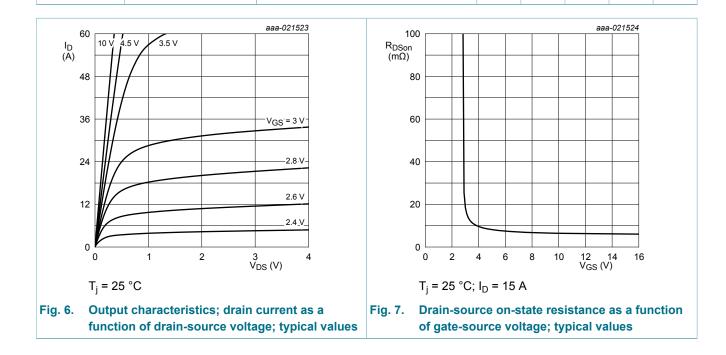
Qr

recovered charge

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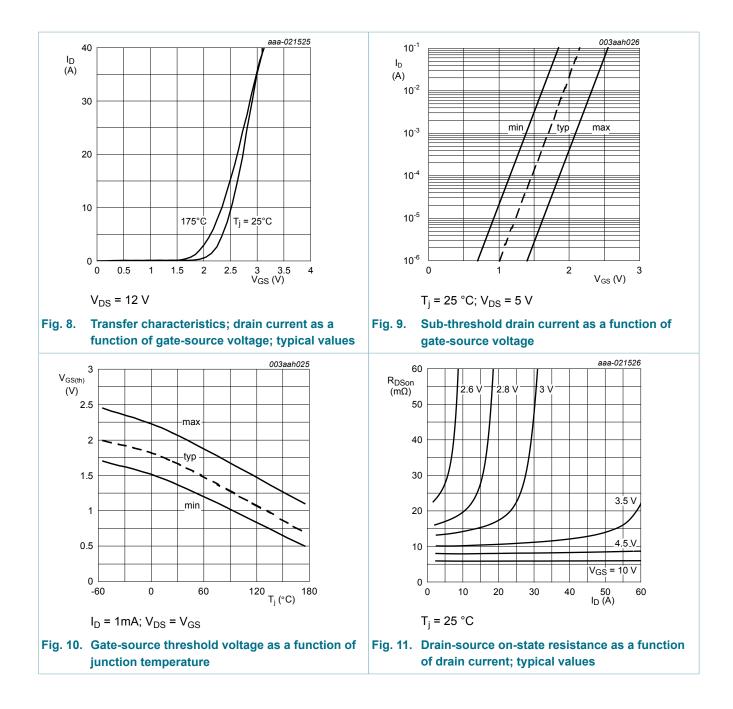
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{GD}	gate-drain charge		-	5.5	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	939	1249	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	201	241	pF
C _{rss}	reverse transfer capacitance	V _{DS} = 25 V; R _L = 1.5 Ω; V _{GS} = 5 V;	-	128	176	pF
t _{d(on)}	turn-on delay time	V_{DS} = 25 V; R_L = 1.5 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; T_j = 25 °C	-	8.8	-	ns
t _r	rise time		-	22	-	ns
t _{d(off)}	turn-off delay time		-	17.8	-	ns
t _f	fall time	-	-	17.2	-	ns
Source-dra	in diode		I			
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	13.9	-	ns
Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	_	4.6	-	nC



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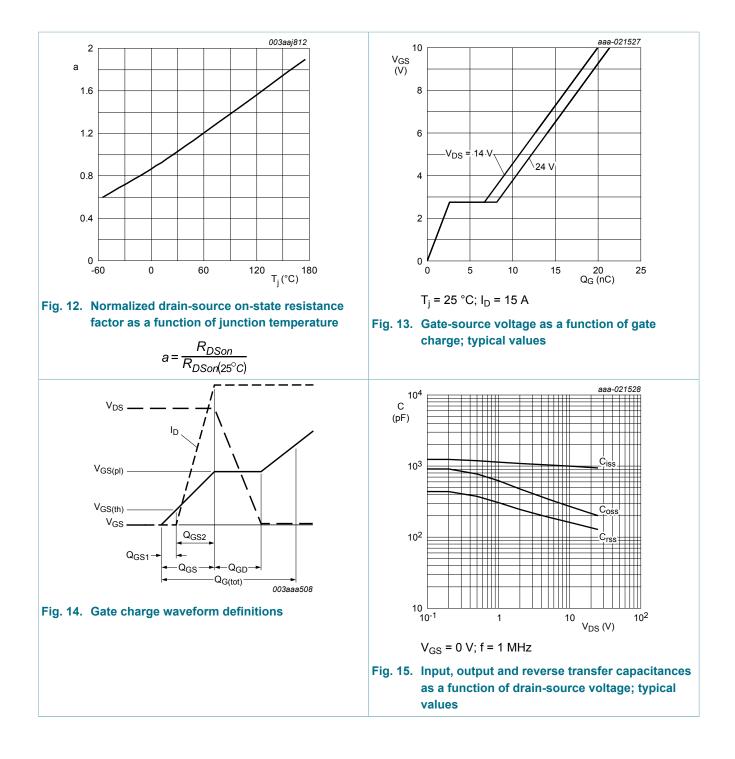
N-channel 30 V, 10 m Ω logic level MOSFET in LFPAK33



7/13

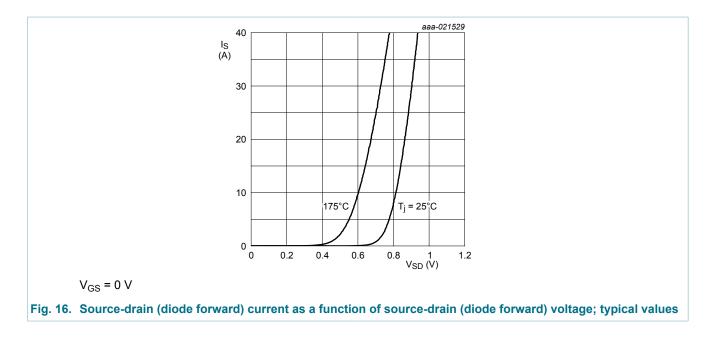
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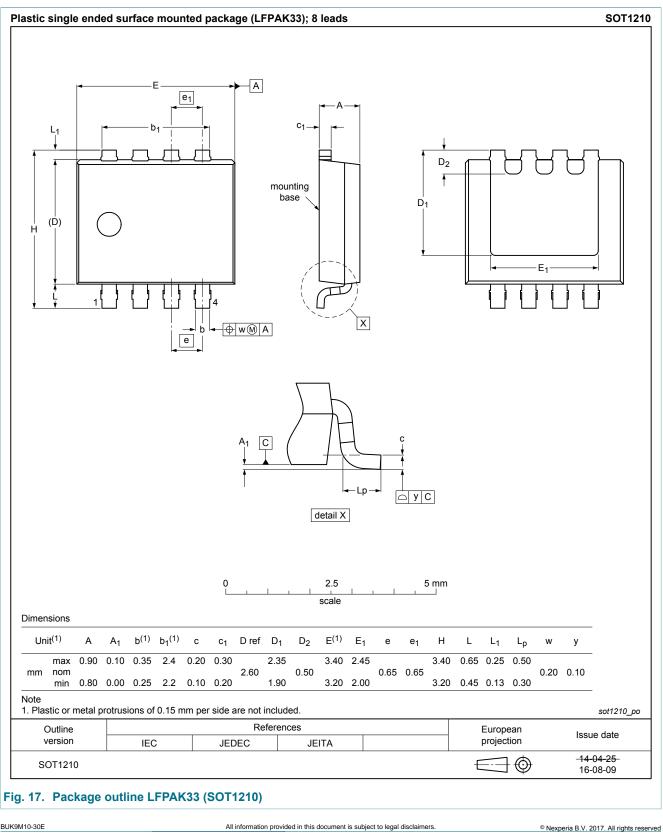


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

N-channel 30 V, 10 mQ logic level MOSFET in LFPAK33

12. Package outline



BUK9M10-30E

Product data sheet

19 September 2016

N-channel 30 V, 10 mΩ logic level MOSFET in LFPAK33

13. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BUK9M10-30E
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19 September 2016

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N-channel 30 V, 10 mQ logic level MOSFET in LFPAK33

14. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Application information	9
12	Package outline	10
13	Legal information	11
13.1		
13.1	Data sheet status	
13.1 13.2	Definitions	11
		11

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BUK9M10-30E



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